

ABSTRACT OF THE DISCLOSURE

We provide a method of doping an Si or SiGe film with carbon or boron. By reducing the silicon precursor pressure, heavily-doped films may be obtained. A single dopant source may be used. The doped Si and SiGe films are of suitable quality for use in a transistor such as an HBT.

He shall not stand alone. *He* *shall* *not* *stand* *alone.*